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N-Channel Power MOSFET

24 V, 9 A, 16 m Ω , Dual ECH8

ECH8655R-R-TL-H

Features

- Low ON-resistance
- 2.5 V Drive
- Common-drain Type
- Protection Diode in
- Built-in Gate Protection Resistor
- Best Suited for LiB Charging and Discharging Switch
- This Device is Pb-Free and are RoHS Compliant

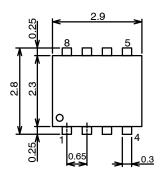
Product & Package Information

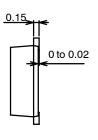
Package: ECH8JEITA, JEDEC: -

• Minimum Packing Quantity: 3,000 Pcs./Reel

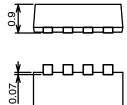
TopView

Unit : mm (typ) 7011A-003





ECH8655R-R-TL-H





3 : Source2 4 : Gate2

5 : Drain

6 : Drain 7 : Drain

8 : Drain

Bottom View ECH8

Figure 1. Package Dimensions

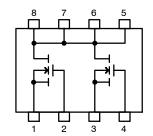


SOT-28FL / ECH8 CASE 318BF

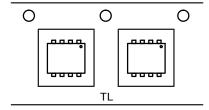
GENERIC MARKING DIAGRAM



ELECTRICAL CONNECTION



PACKING TYPE: TL



ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS at $T_A = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		24	V
Gate-to-Source Voltage	V_{GSS}		±12	V
Drain Current (DC)	I _D		9	Α
Drain Current (Pulse)	I _{DP}	PW ≤[] 0 μs, duty cycle ≤[]%	60	Α
Allowable Power Dissipation	P _D	When mounted on ceramic substrate (900 mm² ×[0.8 mm) 1 unit	1.4	W
Total Dissipation	P _T	When mounted on ceramic substrate (900 mm ² × 0.8 mm)	1.5	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTICS at $T_A = 25^{\circ}C$

			Ratings			
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D = 1 mA, V _{GS} = 0 V	24			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0V			1	μΑ
Gate-to-Source Leakage Current	I _{GSS}	$V_{GS} = \pm 8 \text{ V},$ $V_{DS} = 0 \text{ V}$			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} = 10 V, I _D = 1 mA	0.5		1.3	V
Forward Transfer Admittance	yfs	V _{DS} = 10 V, I _D = 4.5 A	4.8	8		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D = 4.5 A, V _{GS} = 4.5 V	10	13	16	mΩ
	R _{DS} (on)2	I _D = 4.5 A, V _{GS} = 4.0 V	10.5	13.5	16.5	mΩ
	R _{DS} (on)3	I _D = 4.5 A, V _{GS} = 3.1 V	11	15	20	mΩ
	R _{DS} (on)4	I _D = 2 A, V _{GS} = 2.5 V	13	18	24	mΩ
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		320		ns
Rise Time	t _r	rest Circuit.		1100		ns
Turn-OFF Delay Time	t _d (off)	1 [2400		ns
Fall Time	t _f	1		2100		ns
Total Gate Charge	Qg	V _{DS} = 10 V,		16.8		nC
Gate-to-Source Charge	Qgs	V _{GS} = 10 V, I _D = 9 A		1.6		nC
Gate-to-Drain "Miller" Charge	Qgd	1		4.8		nC
Diode Forward Voltage	V_{SD}	I _S = 9 A, V _{GS} = 0 V		0.8	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit

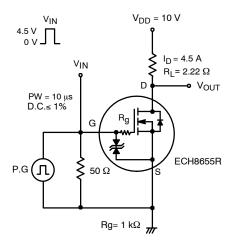


Figure 2. Switching Time Test Circuit

ORDERING INFORMATION

Device	Package	Shipping [†]	Memo
ECH8655R-R-TL-H	ECH8	3,000 pcs./reel	Pb Free and Halogen Free

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

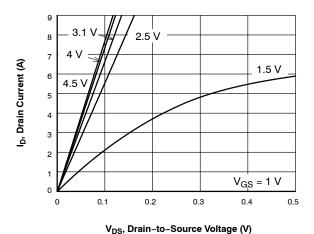
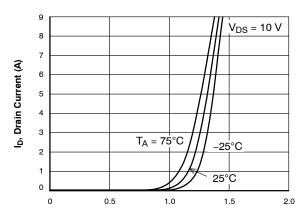


Figure 3. I_D - V_{DS}



V_{GS}, Gate-to-Source Voltage (V)

Figure 4. I_D - V_{GS}

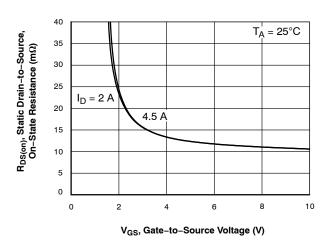


Figure 5. $R_{DS(on)} - V_{GS}$

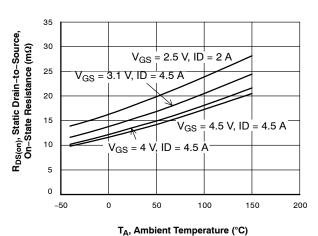


Figure 6. R_{DS(on)} - T_A

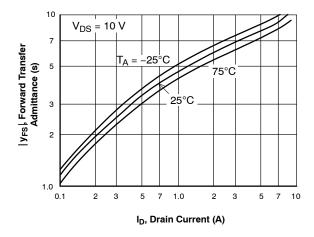


Figure 7. |yfs| - I_D

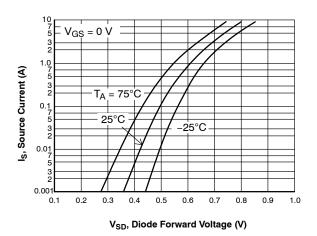


Figure 8. I_S - V_{SD}

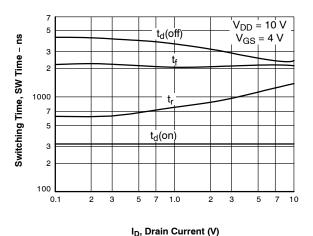
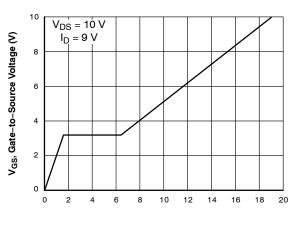
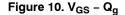
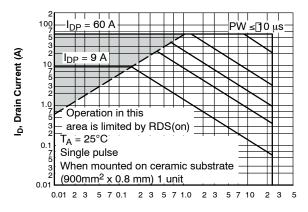


Figure 9. SW Time - I_D



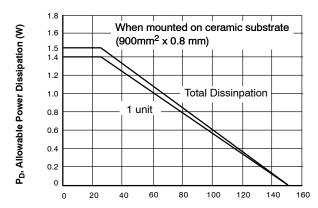
Qg, Total Gate Charge (nC)





V_{DS}, Drain-to-Source Voltage (V)



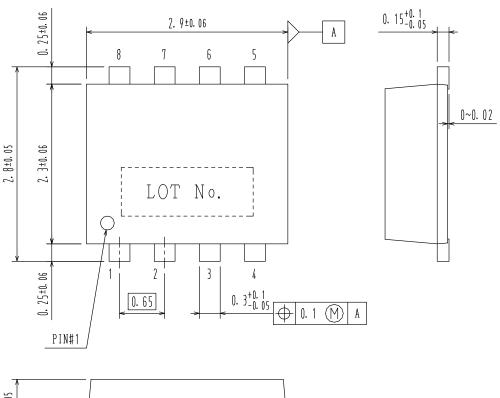


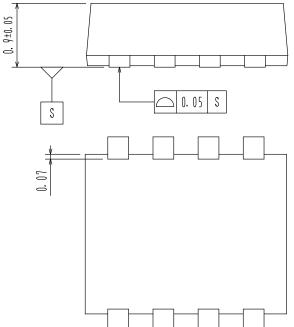
 T_A , Ambinet Temperature (°C)

Figure 12. P_D – T_A

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DATE 31 MAR 2012





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